

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Kiyoshi IRINO

Serial No.: 09/428,052

Filed: October 27, 1999



Group Art Unit: 2815

Examiner: J. Diaz

Amndt
11/1
6-6-01
T. Flanagan

For: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (AS AMENDED)

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: May 24, 2001

Sir:

In response to the Office Action dated January 26, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 8 and 9 without prejudice or disclaimer.

Please amend claims 6, 10 and 13 as follows:

6. (Twice Amended) A method of fabricating a semiconductor device, comprising the steps

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film; and

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